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(54) Title: UNIFORM DRY ETCH IN TWO STAGES

(57) Abstract: A method of etching silicon oxide from a multiple trenches is described which allows more homogeneous etch rates among trenches. The surfaces of the etched silicon oxide within the trench following the etch may also be smoother. The method includes two dry etch stages followed by a sublimation step. The first dry etch stage removes silicon oxide quickly and produces large solid residue granules. The second dry etch stage remove silicon oxide slowly and produces small solid residue granules in amongst the large solid residue granules. Both the small and large solid residue are removed in the ensuing sublimation step. There is no sublimation step between the two dry etch stages.

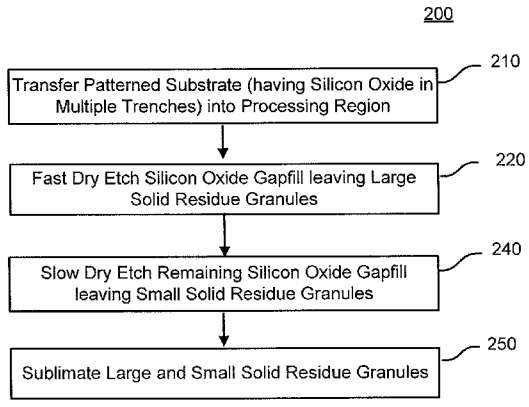


FIG. 2

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Declarations under Rule 4.17:

— *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*

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— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*